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RFMD Expands Industry-Leading GaN Product Portfolio to Support DOCSIS 3.1 Cable Networking at SCTE Cable-Tec Expo

Industry's Broadest Gallium Nitride (GaN) Amplifier Family Allows CATV Operators and MSOs to Easily Upgrade Networks to Meet DOCSIS 3.1 Requirements

DENVER, Sept. 22, 2014 (GLOBE NEWSWIRE) -- **SCTE Cable-Tec Expo** -- RFMD (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency solutions, today unveiled 11 new amplifiers of which six are gallium nitride- (GaN-) based products to support the requirements of the new data over cable service interface specification (DOCSIS) 3.1. RFMD will showcase its portfolio of industry-leading CATV components for customers at its booth/meeting room (#2044) at the SCTE Cable-Tec Expo in Denver from September 22-25.

RFMD's DOCSIS 3.1 family includes 1.2GHz power amplifiers as both hybrids and multi-chip modules (MCMs) that use state of the art GaN HEMT process technology and offer optimal linearity and output power while providing robust reliability. The newest addition to RFMD's product portfolio for DOCSIS 3.1 includes new power doubler amplifiers, push pull amplifiers, optical receivers, a reverse path amplifier, and a family of digital step attenuators. With the addition of these new products, RFMD now offers more than 25 products tailored for DOCSIS 3.1 applications, making it the industry's broadest offering.

RFMD's downstream amplifiers operate from 40MHz to 1.218GHz with extremely low distortion levels and excellent input and output return loss (20dB typical). The reverse path amplifiers work up to 300MHz with high gain and highly integrated functions. RFMD's GaN technology offers the power density required to meet high power CATV requirements. RFMD has been shipping high-volume CATV GaN-based amplifiers for the past five years.

RFMD's award-winning GaN family allows cable operators and MSOs to easily upgrade existing CATV infrastructure to meet the power amplifier requirements of the new DOCSIS 3.1 standard, increasing effective downstream data rates from 160 Megabits per second (Mb/s) to 10 Gigabits per second (Gbit/s), and upstream data rates from 120 Mb/s to 1 Gbit/s when compared to DOCSIS 3.0. Due to the high output and gain benefits derived from RFMD's GaN amplifiers, cable operators can upgrade their existing equipment within current locations, saving on both installation time and cost.

"We continue to expand our family of GaN products, providing cable operators and MSOs an easy, cost-effective upgrade path to DOCSIS 3.1 to extend the life of their existing networks," said Gordon Cook, general manager of RFMD's Power Broadband Business Unit. "RFMD remains the only company shipping GaN amplifiers for CATV in high volumes and in the device and MCM packages customers need today, and we look forward to sharing additional information about this growing family of products at the SCTE Cable-Tec Expo."

About RFMD

RFMD (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance radio frequency solutions. RFMD's products enable worldwide mobility, provide enhanced connectivity, and support advanced functionality in the mobile device, wireless infrastructure, wireless local area network (WLAN or Wi-Fi), cable television (CATV)/broadband, Smart Energy/advanced metering infrastructure (AMI), and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises, and communications equipment providers. RFMD is an ISO 9001-, ISO 14001-, and ISO/TS 16949-certified manufacturer with worldwide engineering, design, sales and service facilities. For more information, please visit RFMD's web site at rfmd.com.

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in operating results, the inability of certain of our customers or suppliers to access their

traditional sources of credit, our industry's rapidly changing technology, our dependence on a few large customers for a substantial portion of our revenue, our ability to implement innovative technologies, our ability to bring new products to market and achieve design wins, the efficient and successful operation of our wafer fabrication facilities, assembly facilities and test and tape and reel facilities, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, variability in manufacturing yields, industry overcapacity and current macroeconomic conditions, inaccurate product forecasts and corresponding inventory and manufacturing costs, dependence on third parties and our ability to manage channel partners and customer relationships, our dependence on international sales and operations, our ability to attract and retain skilled personnel and develop leaders, the possibility that future acquisitions may dilute our shareholders' ownership and cause us to incur debt and assume contingent liabilities, fluctuations in the price of our common stock, additional claims of infringement on our intellectual property portfolio, lawsuits and claims relating to our products, security breaches and other similar disruptions compromising our information and exposing us to liability, the impact of stringent environmental regulations, and the receipt of required regulatory and shareholder approvals related to our proposed business combination with TriQuint Semiconductor, Inc. and the completion of the proposed transaction. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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